



GL21N50FA9

Silicon N-Channel Power MOSFET

General Description

GL21N50FA9, the silicon N-channel Enhanced VDMOSFET, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220F, which accords with the RoHS standard.

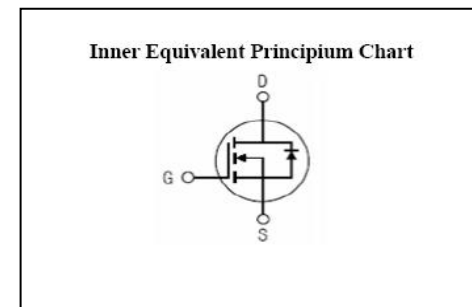
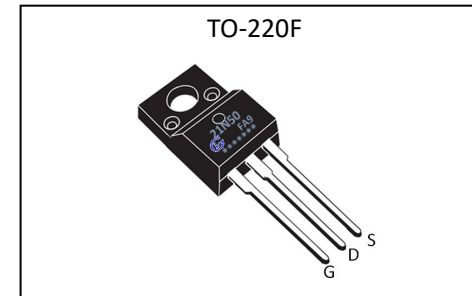
Features

- Fast Switching
- Low ON Resistance(Typical Data:0.21Ω)
- Low Gate Charge Minimize Switching loss
- Fast Recovery Body Diode
- 100% Single Pulse avalanche energy Test

Applications

- Adaptor
- Charger
- SMPS Standby Power

$V_{DSS}(T_c=150^{\circ}C)$	500	V
I_D	21	A
$P_D(T_c=25^{\circ}C)$	55	W
$R_{DS(ON).type.}$	0.21	Ω



Absolute (Tc=25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage ^{*1}	500	V
I_D	Continuous Drain Current	21	A
I_{DM}	Pulsed Drain Current at $V_{GS}=10V^{*2}$	82	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulse Avalanche Energy	1500	mJ
I_{AS}	Avalanche Current	6.8	A
dv/dt	Peak Diode Recovery dv/dt^{*3}	5.0	V/ns
P_D	Power Dissipation	55	W
	Derating Factor above 25°C	0.44	W/°C
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150,-55 to 150	°C
T_L	Maximum Temperature for Soldering	300	°C

Caution Stresses greater than those in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	Rating	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.27	°C/ W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	°C/ W



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Electrical Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

OFF Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	500	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=500V, V_{GS}=0V, T_a=25^\circ\text{C}$	--	--	1.0	μA
		$V_{DS}=400V, V_{GS}=0V, T_a=125^\circ\text{C}$	--	--	100	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+30V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-30V$	--	--	-100	nA

ON Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance ^{*4}	$V_{GS}=10V, I_D=10.5A$	--	0.21	0.25	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	--	4.0	V
g_{fs}	Forward Transconductance ^{*4}	$V_{DS}=15V, I_D=10.5A$	--	17	--	S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=25V$ $f=1.0\text{MHz}$	--	2864	--	pF
C_{oss}	Output Capacitance		--	286	--	
C_{rss}	Reverse Transfer Capacitance		--	25	--	

Resistive Switching Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=21A, V_{DD}=250V$ $V_{GS}=10V, R_g=25\Omega$	--	33	--	ns
t_r	Rise Time		--	75	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	181	--	
t_f	Fall Time		--	83	--	
Q_g	Total Gate Charge	$I_D=21A, V_{DD}=250V$ $V_{GS}=10V$	--	63	--	nC
Q_{gs}	Gate to Source Charge		--	14	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	24	--	



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Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_{SD}	Continuous Source Current (Body Diode)		--	--	21	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	80	A
V_{SD}	Diode Forward Voltage	$I_S=21A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=21A, T_J=25^{\circ}C$	--	392	--	ns
Q_{rr}	Reverse Recovery Charge	$dI_F/dt=100A/\mu s, V_{GS}=0V$	--	3.36	--	μC

*1: $T_J = +25^{\circ}C$ to $+150^{\circ}C$

*2: Repetitive rating; pulse width limited by maximum junction temperature.

*3: $I_{SD}=20A, di/dt < 100A/\mu s, V_{DD} < BV_{DSS}, T_J = +150^{\circ}C$.

*4: Pulse width $< 380\mu s$; duty cycle $< 2\%$.

Characteristics Curves

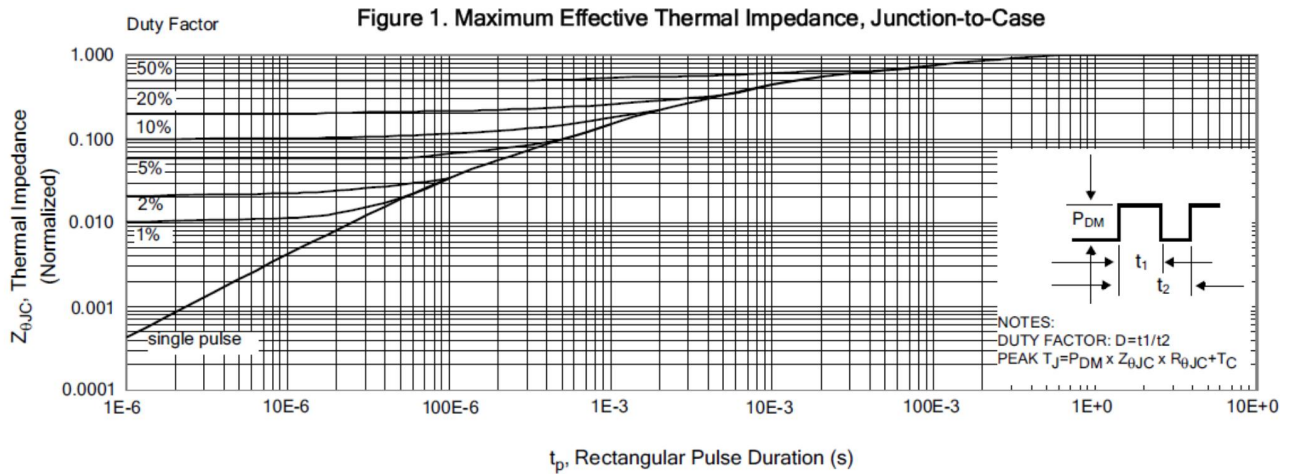


Figure 2. Maximum Power Dissipation vs Case Temperature

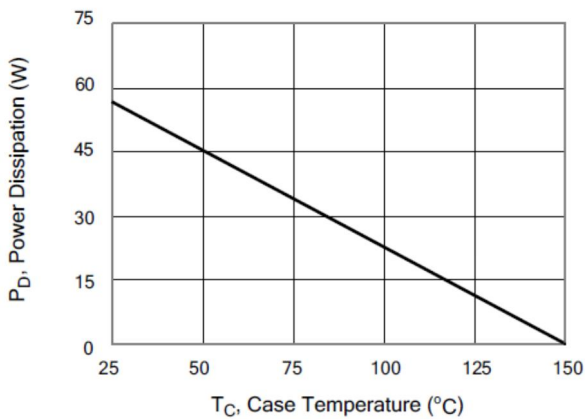


Figure 3. Maximum Continuous Drain Current vs Case Temperature

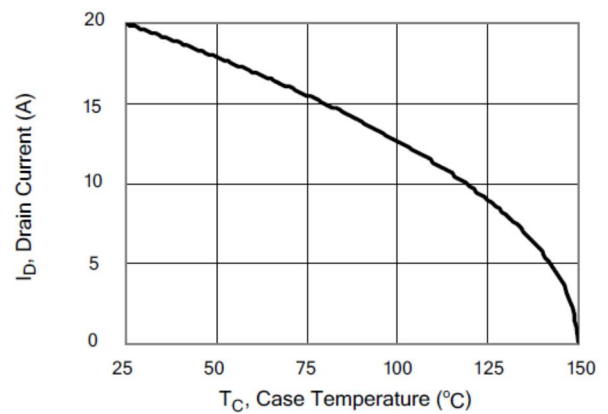


Figure 4. Typical Output Characteristics

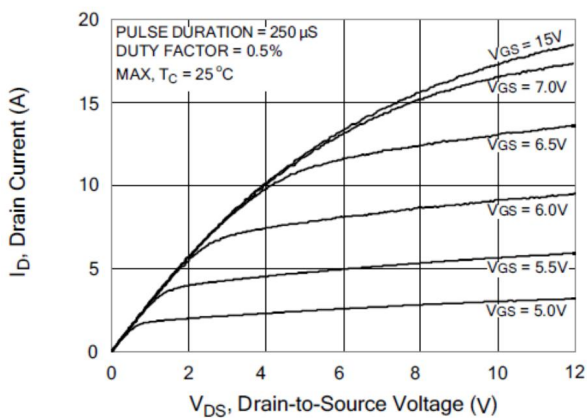
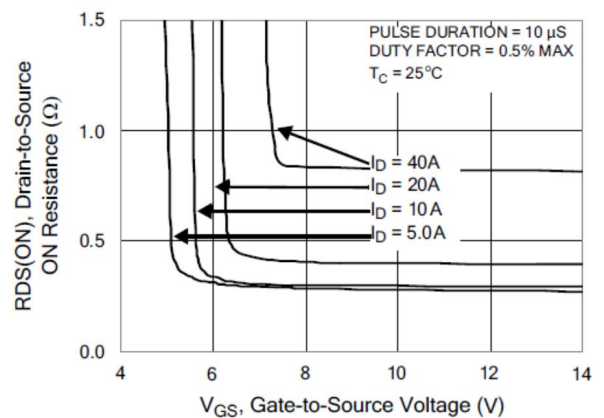


Figure 5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current





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Figure 6. Maximum Peak Current Capability

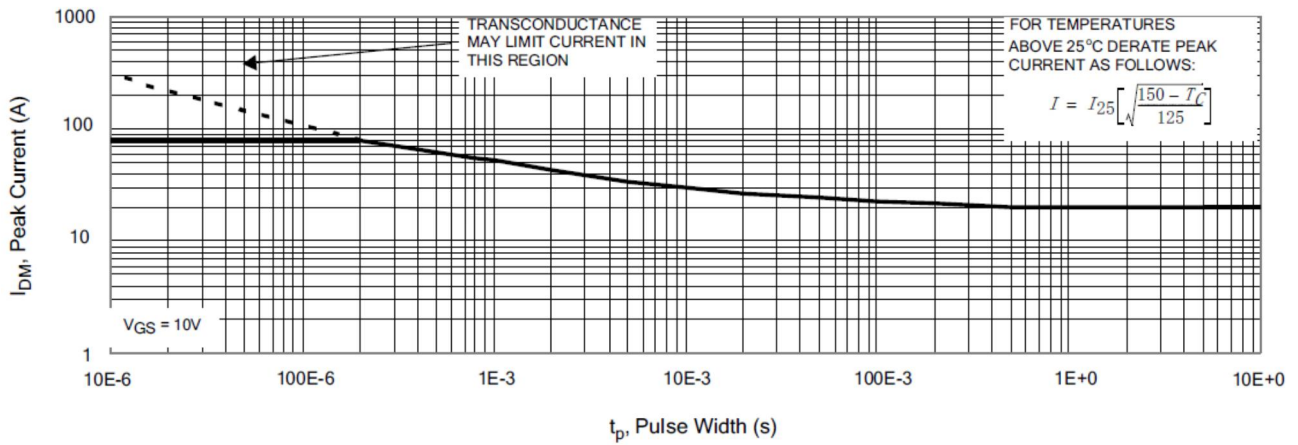


Figure 7. Typical Transfer Characteristics

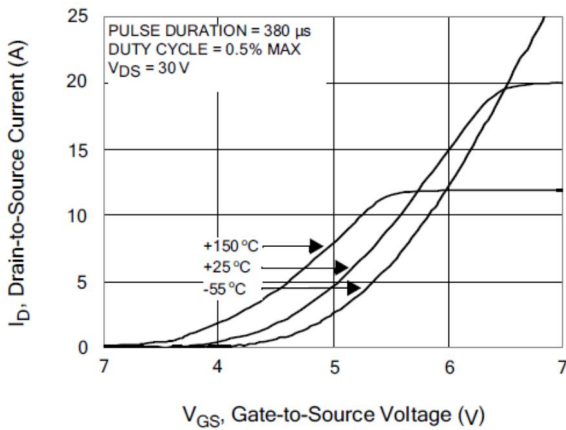


Figure 8. Unclamped Inductive Switching Capability

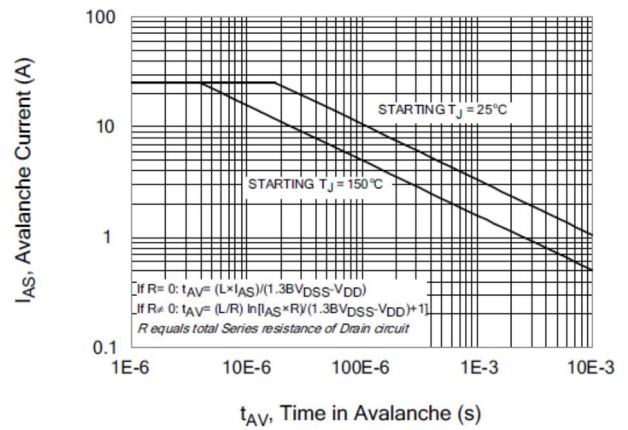


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

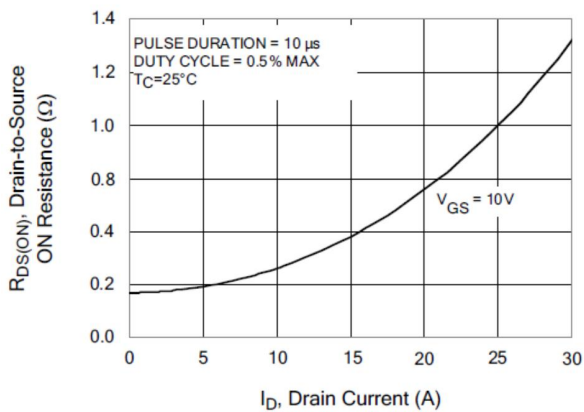
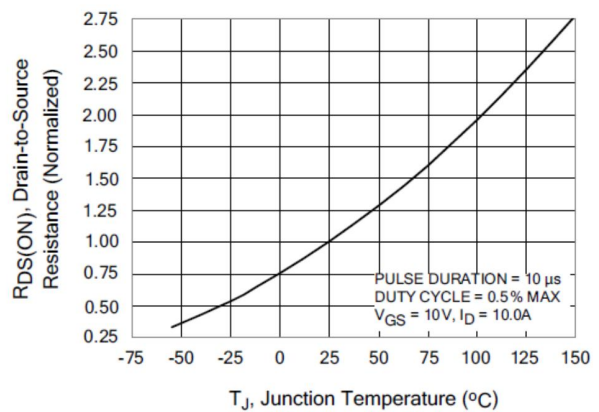


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature



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Figure 11. Typical Breakdown Voltage vs Junction Temperature

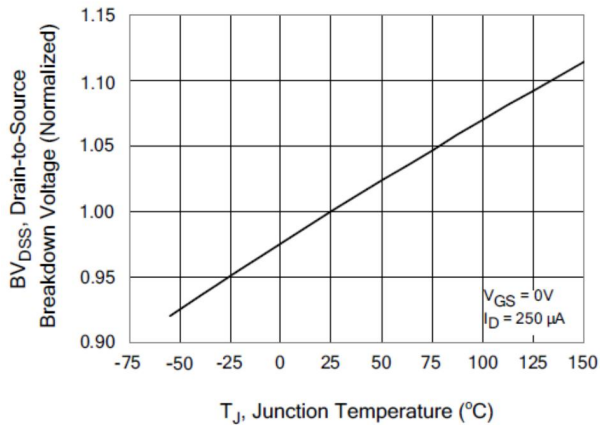


Figure 12. Typical Threshold Voltage vs Junction Temperature

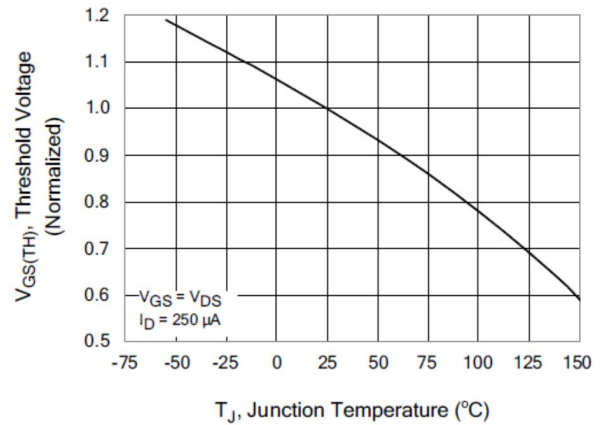


Figure 13. Maximum Forward Bias Safe Operating Area

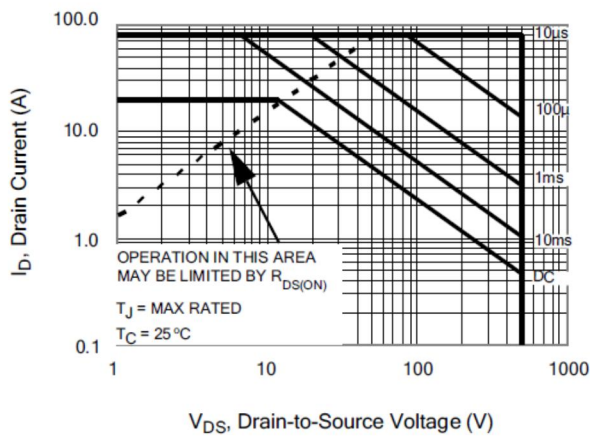


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

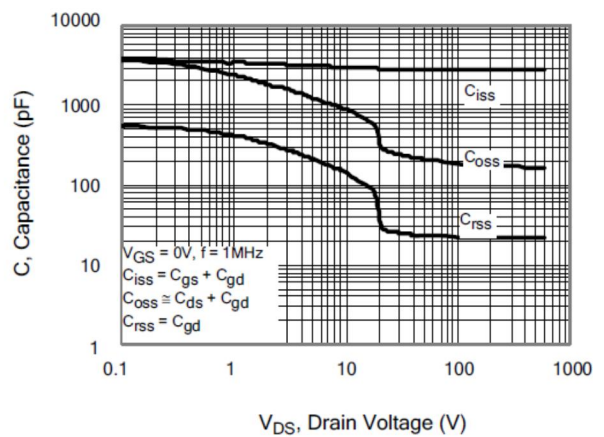


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

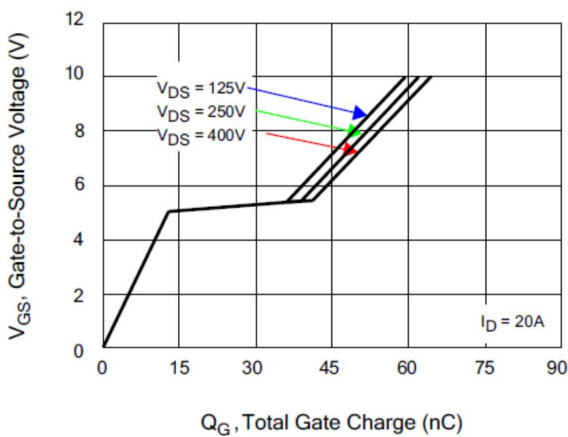


Figure 16. Typical Body Diode Transfer Characteristics

